

Alpha & Omega Semiconductor Product Reliability Qualification Report

AOC2870C rev A

ALPHA & OMEGA Semiconductor, Inc

www.aosmd.com

This report delineates the product's quality and reliability test outcomes. Specific sample sizes undergo accelerated environmental tests, with corresponding electrical testing before and after each interval. Analysis of the conclusive electrical test results affirms the product's adherence to AOS quality and reliability standards in accordance with **JEDEC**. Reference to the existing qualification outcomes for similar products is warranted due to structural similarities. The released product will be classified by its process family and undergo regular monitoring to ensure continual enhancements in product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Duration	Lots/SS	Number of Failures	Reference Standard
HTGB <i>High Temperature Gate Bias</i>	150°C, Vgs=10V	1000 hrs	3 * 77	0/231	JESD22-A108
HTRB <i>High Temperature Reverse Bias</i>	150°C Vds=100% of Vdsmax	1000 hrs	3 * 77	0/231	JESD22-A108
PC <i>Precondition</i>	168 hrs, 85°C, 85%RH, 3 cycles reflow @ 260°C (<u>MSL 1</u>)	-	9 * 77	0/693	JESD22-A113 J-STD-020
AC* <i>Autoclave</i>	121°C, 100%RH, 15psig	96 hrs	3 * 77	0/231	JESD22-A102
TC* <i>Temperature Cycling</i>	-65°C to 150°C, air to air	1000 cycles	3 * 77	0/231	JESD22-A104
IOL* <i>Intermittent Operational Life</i>	$\Delta T_j = 100^\circ\text{C}$ $t_{on} = 2 \text{ minutes}$ $t_{off} = 2 \text{ minutes}$	15000 cycles	3 * 77	0/231	MIL-STD-750 Method 1037
ESD_HBM	Class 2 (2000V to <4000V)	-	3 pcs	-	JS-001
ESD_CDM	Class C3 (≥1000V)	-	3 pcs	-	JS-002

Notes:

* For SMD devices reliability stress tests performed after PC (precondition).

II. Reliability Evaluation

FIT rate (per billion): 7.63

MTTF = 14960 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

At 60% Confidence Level

Failure Rate = $\text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 7.63$

MTTF = $10^9 / \text{FIT} = 14960$ years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

H = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions ($E_a = 0.7\text{eV}$ and $T_{J u} = 55^\circ\text{C}$)

Acceleration Factor [**Af**] = **Exp** [$E_a / k (1/T_{J u} - 1/T_{J s})$]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

T_{J s} = Stressed junction temperature in degree (Kelvin), $K = C + 273.16$

T_{J u} = The use junction temperature in degree (Kelvin), $K = C + 273.16$

k = Boltzmann's constant, $8.617164 \times 10^{-5} \text{eV} / K$